

1. Material Substrate GaAs (N Type)
Epitaxial Layer GaAlAs (P/N Type)

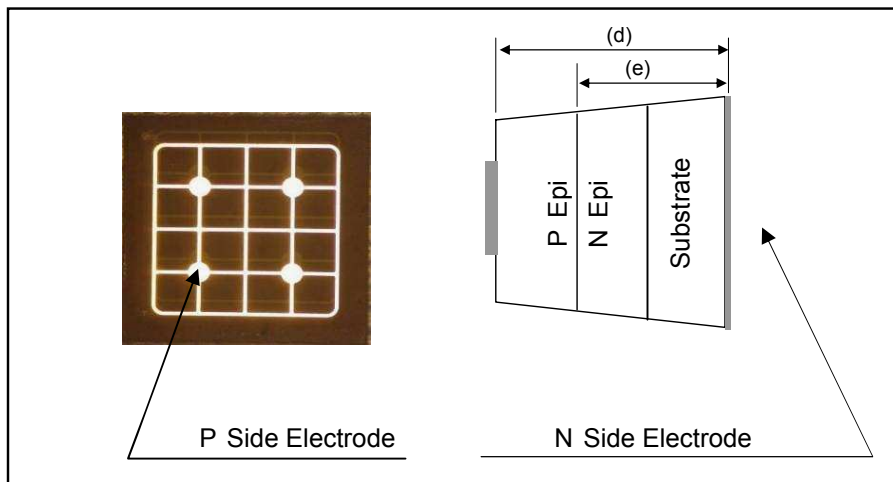
2. Electrode N(Cathode) Side Gold Alloy
P(Anode) Side Gold Alloy

3. Electro-Optical Characteristics

Parameter	Symbo	Min	Typ	Max	Unit	Condition
Forward Voltage	V_F			1.3	V	IF=250mA
Reverse Voltage	V_R	5			V	IR=10uA
Radiant Power	P_O		7		mW	IF=250mA
Wavelength	λ_P		940		nm	IF=20mA
	$\Delta\lambda$		45		nm	IF=20mA

※ Note : LED Chip is mounted on TO-18 gold header without resin coating.

4. Mechanical Data (a) Emission Area ----- 58.5mil x 58.5mil
 (b) Bottom Area ----- 60.0mil x 60.0mil
 (c) Bonding Pad ----- 128um
 (d) Chip Thickness ----- 11mil
 (e) Junction Height ----- 6.7mil



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